L Number	Hits	Search Text	DB	Time stamp
1	95	(cronon or via) and	USPAT;	2003/01/02 17:05
	1	((trench or via) near (barrier or SiN or	US-PGPUB;	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
		(etch adj stop) or Ta or TaN or Wn or WN or	EPO; JPO;	
		tantalum))	DERWENT;	
2	13	((substrate near (trench or via)) and	IBM_TDB	2002/02/02 15 02
		((trench or via) near (barrier or SiN or	USPAT; US-PGPUB;	2003/01/02 16:01
		(etch adj stop) or Ta or TaN or Wn or WN or	EPO; JPO;	
		tantalum))) and ((siliocn or si) with	DERWENT;	
		substrate)	IBM TDB	
3	72	((substrate near (trench or via)) and	USPAT;	2003/01/02 16:09
		((trench or via) near (barrier or SiN or	US-PGPUB;	
		(etch adj stop) or Ta or TaN or Wn or tantalum))) and ((silicon or si) with	EPO; JPO;	
		substrate)	DERWENT;	
4	54	· ·	IBM_TDB USPAT;	2003/01/02 16:39
		((trench or via) near (barrier or SiN or	US-PGPUB;	2003/01/02 16:39
		(etch adj stop) or Ta or TaN or Wn or WN or	EPO; JPO;	
		tantalum))) and ((silicon or si) with	DERWENT;	
5	0	substrate)) and (@ad<20010501)	IBM_TDB	
	0	(substrate near (trench or via)) and ((trench or via) near (trench or via or	USPAT;	2003/01/02 16:40
		groove) near (SiN or (etch adj stop) or Ta	US-PGPUB;	
		or TaN or Wn or wn or tantalum))	EPO; JPO; DERWENT;	
		our of sancaram,	IBM TDB	
6	10	1 (Table 1 and 1 and 1 and 1 and 1	USPAT;	2003/01/02 16:37
		((trench or via) near (trench or via or	US-PGPUB;	2003/01/02 10.3/
		groove) with (SiN or (etch adj stop) or Ta	EPO; JPO;	
		or TaN or Wn or WN or tantalum))	DERWENT;	
7	576	257/758.ccls. and (SiN or (etch adj stop) or	IBM_TDB	
1		Ta or Tan or Wn or Wn or tantalum)	USPAT; US-PGPUB;	2003/01/02 16:39
		our datam,	EPO; JPO;	
			DERWENT;	
8	450	(055 (550	IBM_TDB	
l° (459	i terification and the terification and second	USPAT;	2003/01/02 17:06
		or Ta or TaN or Wn or WN or tantalum)) and (@ad<20010501)	US-PGPUB;	
		(300.20010301)	EPO; JPO; DERWENT;	
	i		IBM TDB	
9	350		USPAT;	2003/01/02 17:03
		or Ta or TaN or Wn or WN or tantalum)) and	US-PGPUB;	, , , , , , , , , , , , , , , , , , , ,
		(@ad<20010501)) and (trench or via or groove)	EPO; JPO;	
		9100ve/	DERWENT;	
10	1342	trench adj gate	IBM_TDB	2002/03/00 45
		3 3 · -	USPAT; US-PGPUB;	2003/01/02 17:04
			EPO; JPO;	
			DERWENT;	
11	630	(trough add make)	IBM_TDB	
	629	(trench adj gate) and (gate near oxide)	USPAT;	2003/01/02 17:04
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
12	725	(trench adj gate) and (gate near (oxide or	USPAT;	2003/01/02 17:05
		sio or dielectric))	US-PGPUB;	1, 12, 02 17,03
			EPO; JPO;	
	İ		DERWENT;	
13	260	((trench adj gate) and (gate near (oxide or	IBM_TDB	2002/01/20
		sio or dielectric))) and (barrier or SiN or	USPAT; US-PGPUB;	2003/01/02 17:06
		(etch adj stop) or Ta or TaN or Wn or WN or	EPO; JPO;	
		tantalum)	DERWENT;	
14	206	///twomph and and a	IBM_TDB	
-7	206	(((trench adj gate) and (gate near (oxide or	USPAT;	2003/01/02 17:06
		sio or dielectric))) and (barrier or SiN or (etch adj stop) or Ta or TaN or Wn or WN or	US-PGPUB;	
İ		tantalum)) and (@ad<20010501)	EPO; JPO;	
		(544/20010301)	DERWENT; IBM TDB	
			TOU IND	

15	117	((((trench adj gate) and (gate near (oxide	USPAT;	2003/01/02 17:12
		or sio or dielectric))) and (barrier or SiN	US-PGPUB;	
		or (etch adj stop) or Ta or TaN or Wn or WN	EPO; JPO;	
		or tantalum)) and (@ad<20010501)) and ((gate	DERWENT;	
		or trench) with (barrier or SiN or (etch adj	IBM_TDB	
		stop) or Ta or TaN or Wn or WN or tantalum))	_	
16	50	(((trench adj gate) and (gate near (oxide	USPAT;	2003/01/02 17:12
		or sio or dielectric))) and (barrier or SiN	US-PGPUB;	
		or (etch adj stop) or Ta or TaN or Wn or WN	EPO; JPO;	
		or tantalum)) and (@ad<20010501)) and ((gate	DERWENT;	
		or trench) with (SiN or (etch adj stop) or	IBM_TDB	
		Ta or TaN or Wn or WN or tantalum))		
-	2	(("5268326") or ("5091330")).PN.	USPAT;	2003/01/02 15:55
			US-PGPUB	